



Product Summary

BV _{DSS}	Rds(on) Max	I⊳ Tc = +25°C (Note 9)
40V	3.3mΩ @ V _{GS} = 10V	100A
40 V	5.0mΩ @ VGS = 5V	95A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- BLDC motors
- DC-DC converters
- Load switches

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable And Robust End Application

PowerDI5060-8

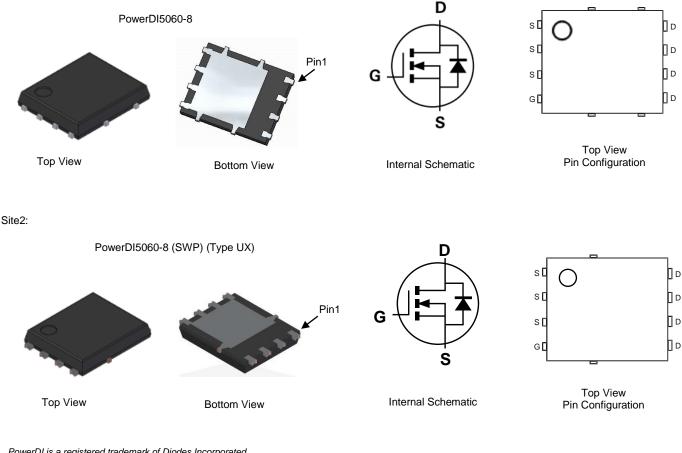
- Low R_{DS(ON)} Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH43M8LPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.097 grams (Approximate)

Site1:



PowerDI is a registered trademark of Diodes Incorporated.

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Notes:

Ordering Information (Note 4)

Part Number	Backago	Packing		
Fait Nulliper	Package	Qty.	Carrier	
DMTH43M8LPSQ-13	PowerDI5060-8	2,500	Tape & Reel	
DMTH43M8LPSQ-13	PowerDI5060-8 (SWP) (Type UX)	2,500	Tape & Reel	

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

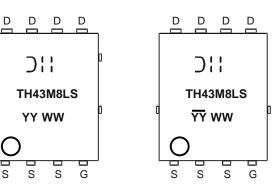
Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



PowerDI5060-8 (SWP) (Type UX)



 \Box_{i} =Manufacturer's Marking TH43M8LS = Product Type Marking Code YYWW or YYWW = Date Code Marking YY or YY = Year Code (ex: 22 = 2022) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	Vdss	40	V	
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	T _A = +25°C T _A = +100°C	lD	22 15.5	A
Continuous Drain Current, V _{GS} = 10V (Note 6) (Note 9)	Tc = +25°C Tc = +100°C	ID	100 82	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		ldм	350	А
Maximum Continuous Body Diode Forward Current (Note 6)		ls	69	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycl	e = 1%)	I _{SM}	350	А
Avalanche Current, L = 1mH		las	13.2	A
Avalanche Energy, L = 1mH		Eas	87	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)		Reja	55	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	PD	83	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	1.8	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

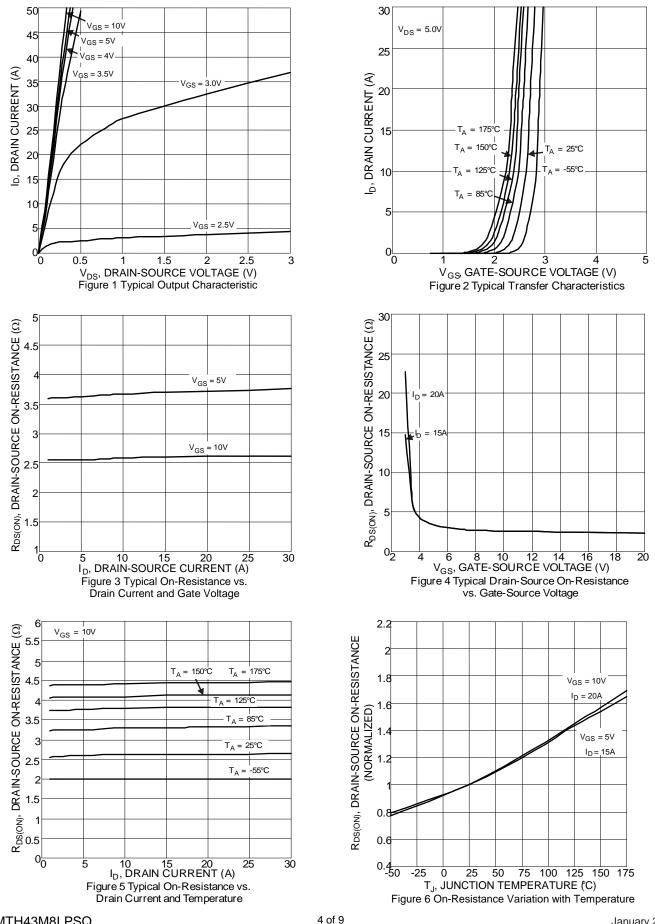
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

<u>Ob exectoristic</u>	Currenche e l	Min	True	Max	11	Test Condition	
	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	D) (40		1	V		
Drain-Source Breakdown Voltage	BV _{DSS}	40			V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS		_	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)			1	1			
Gate Threshold Voltage	Vgs(th)	1	—	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance ($T_c = +25^{\circ}C$)	Pro(on)	_	2.7	3.3	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Dialit-Source Off-Resistance ($TC = +25$ C)	RDS(ON)	—	3.6	5.0	11152	VGS = 5V, ID = 15A	
Static Drain-Source On-Resistance ($T_C = +175^{\circ}C$) (Note 8)	Rds(on)	_	4.7	—	mΩ	V _{GS} = 10V, I _D = 20A	
Diode Forward Voltage	Vsd	_	—	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)						÷	
Input Capacitance	Ciss	—	2,693	3,367	pF	$V_{DS} = 20V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	_	850	1105			
Reverse Transfer Capacitance	Crss	_	52	104			
Gate Resistance	Rg	_	2.54	5.1	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Q _G		38.5	49		V _{DS} = 20V, I _D = 20A	
Total Gate Charge (V _{GS} = 4.5V)	QG	_	17.6	22			
Gate-Source Charge	Qgs	_	6.9	11	nC		
Gate-Drain Charge	Q _{GD}		6.9	11			
Turn-On Delay Time	t _{D(ON)}	_	5.2	10		$V_{DD} = 20V, V_{GS} = 10V,$ $I_D = 20A, R_G = 1.6\Omega$	
Turn-On Rise Time	t _R		5.7	11	ns		
Turn-Off Delay Time	tD(OFF)	_	23.5	46			
Turn-Off Fall Time	t _F	_	11	22	1		
Body Diode Reverse Recovery Time	trr	_	35.4	70	ns	1 154 1/4 1004/	
Body Diode Reverse Recovery Charge	Q _{RR}	_	32.9	_	nC	— I _F = 15A, di/dt = 100A/μs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.
Package limit. Notes:



DMTH43M8LPSQ



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V_{GS} = 5V, I_D = 15A

25

50

T., JUNCTION TEMPERATURE (°C)

0

 $V_{GS} = 10V, I_{D} = 20A$

75

100

8

7

6

5

4

3

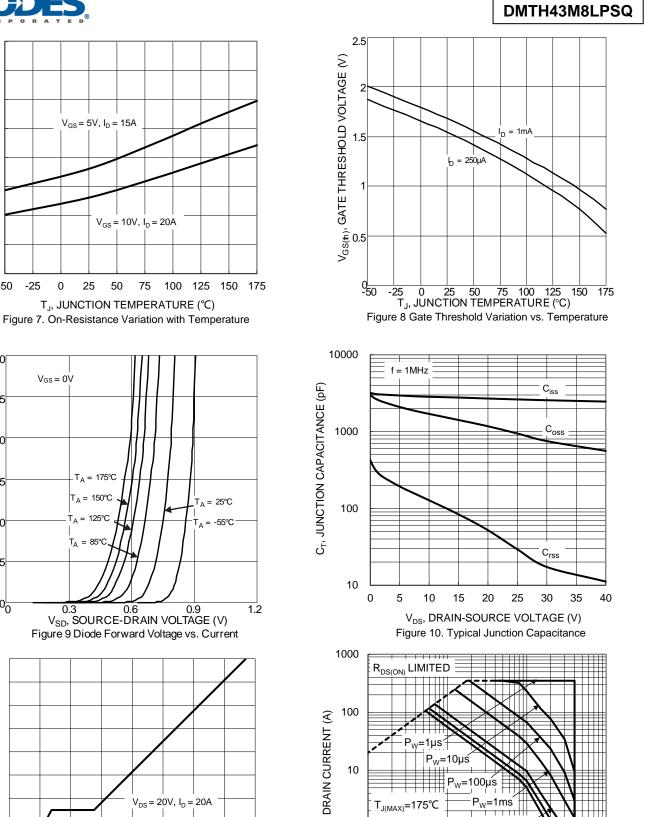
2

1

0

-50 -25

 $R_{\text{DS}(\text{ON})},$ DRAIN-SOURCE ON-RESISTANCE ($\Omega)$



P_w=100µs

T_{J(MAX)}=175°C

Single Pulse

DUT on infinite heatsink

1

T_c=25°C

V_{GS}=10V

P_w=1ms

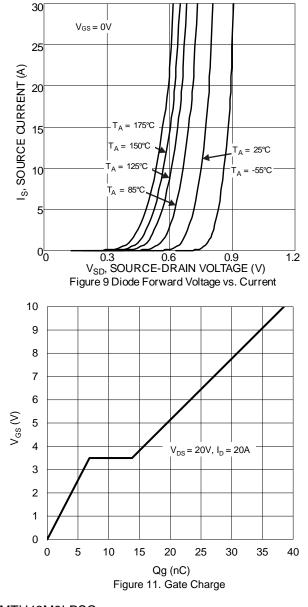
V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area

P_w=10ms

P_w=100ms

10



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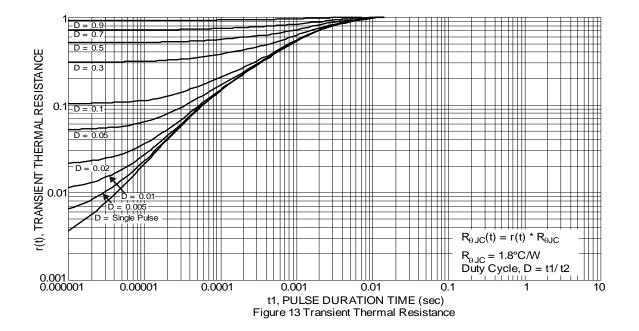
1

0.1

0.1

100



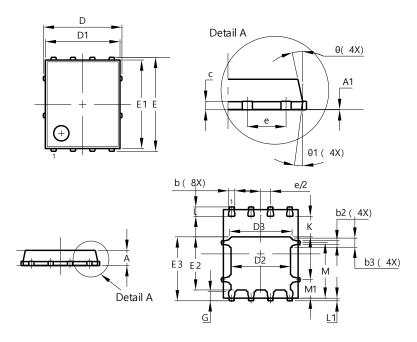




Package Outline Dimensions

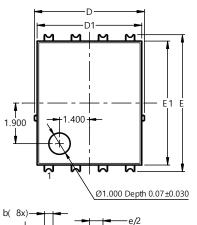
Please see http://www.diodes.com/package-outlines.html for the latest version.

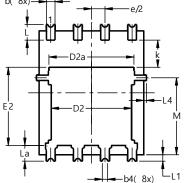
Site1

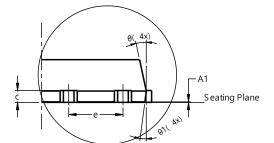


	PowerDI5060-8				
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
E		6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е		1.27 BSC	;		
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
Al	All Dimensions in mm				

Site2

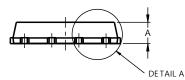






PowerDI5060-8 (SWP) (Type UX)

DE TAIL A



PowerDI5060-8 (SWP) (Type UX)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4	().25REF	-	
c	0.230		0.277	
D	5	.15 BS0	2	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
E	6	.40 BS0	2	
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a		4.595		
е	1	.27BSC	<u>) </u>	
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0	.050RE		
L4	0.025	0.225	0.125	
М	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All	All Dimensions in mm			

PowerDI5060-8

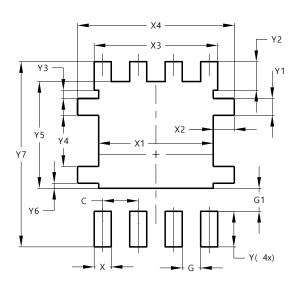


Suggested Pad Layout

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Site1:

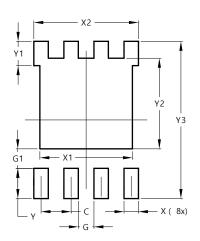
PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site2:

PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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